

1、General Description

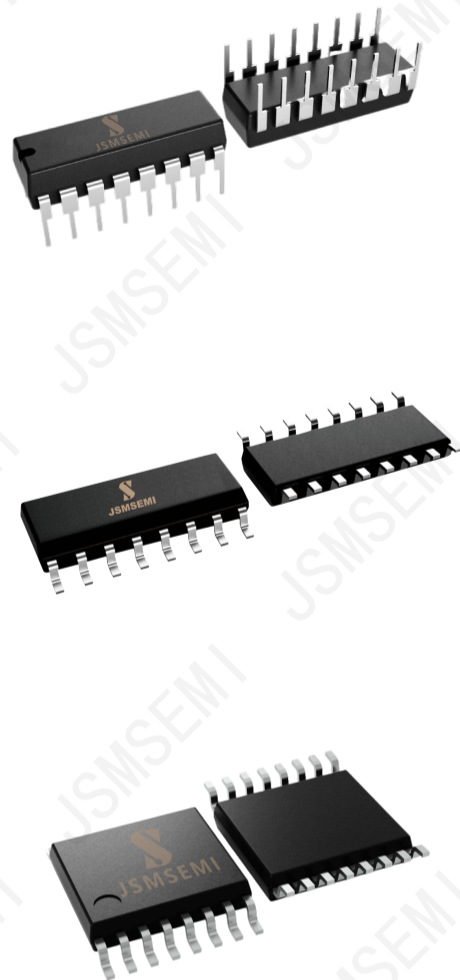
The 74HC/HCT4052 is a dual single-pole quad-throw analog switch ($2 \times \text{SP4T}$) suitable for use in analog or digital 4:1 multiplexer/demultiplexer applications. Each switch features four independent inputs/outputs ($nY0$, $nY1$, $nY2$ and $nY3$) and a common input/output (nZ). A digital enable input ($\bar{E}$) and two digital select inputs ($S0$ and $S1$) are common to both switches. When $\bar{E}$ is HIGH, the switches are turned off. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

Features:

- Wide analog input voltage range from -4.5V to $+4.5\text{V}$
- Low ON resistance:
 - $80\ \Omega$ (typical) at $V_{CC}-V_{EE}=4.5\text{V}$
 - $70\ \Omega$ (typical) at $V_{CC}-V_{EE}=6.0\text{V}$
 - $60\ \Omega$ (typical) at $V_{CC}-V_{EE}=9.0\text{V}$
- Typical “break before make” built-in
- Input levels:
 - For 74HC4052: CMOS level
 - For 74HCT4052: TTL level
- Specified from -40°C to $+125^\circ\text{C}$
- Packaging information: DIP16/SOP16/SSOP16/TSSOP16

Applications:

- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating



2、Block Diagram And Pin Description

2.1、Block Diagram

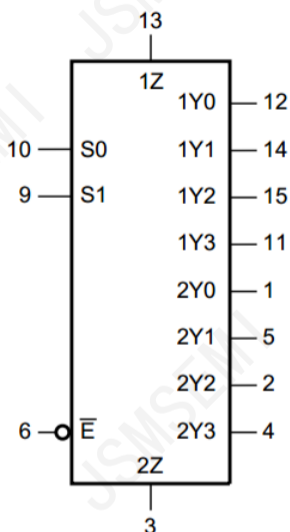


Figure 1. Logic symbol

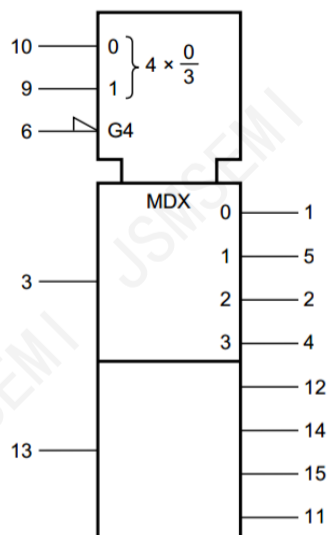


Figure 2. IEC logic symbol

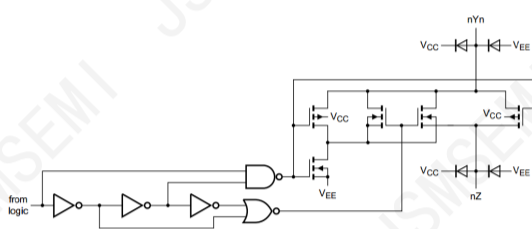


Figure 3. Schematic diagram (one switch)

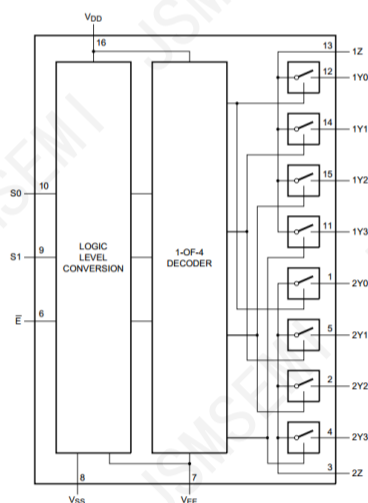
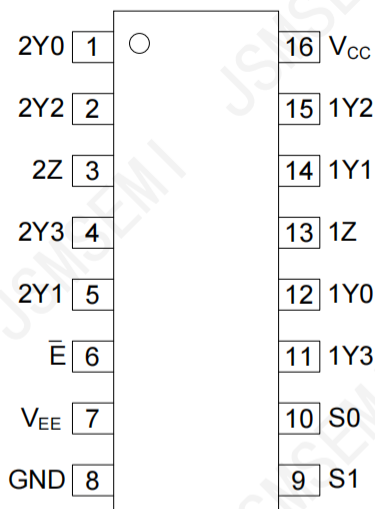


Figure 4. Functional diagram

2.2、Pin Configurations



2.3、Pin Description

Pin No.	Pin Name	Description
1	2Y0	independent input or output
2	2Y2	independent input or output
3	2Z	common input or output
4	2Y3	independent input or output
5	2Y1	independent input or output
6	$\bar{E}$	enable input (active LOW)
7	V_{EE}	negative supply voltage
8	GND	ground supply voltage
9	S1	select logic input
10	S0	select logic input
11	1Y3	independent input or output
12	1Y0	independent input or output
13	1Z	common input or output
14	1Y1	independent input or output
15	1Y2	independent input or output
16	V_{CC}	positive supply voltage

2.4、Function Table

Input			Channel ON
$\bar{E}$	S1	S0	
L	L	L	nY0 and nZ
L	L	H	nY1 and nZ
L	H	L	nY2 and nZ
L	H	H	nY3 and nZ
H	X	X	none

Note: H=HIGH voltage level; L=LOW voltage level; X=don't care.

3、Electrical Parameter

3.1、Absolute Maximum Ratings

(Voltages are referenced to $V_{EE} = \text{GND}$ (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Max.	Unit
supply voltage	V_{CC}	- [1]	-0.5	+11	V
input clamping current	I_{IK}	$V_I < -0.5 \text{ V}$ or $V_I > V_{CC} + 0.5 \text{ V}$	-	± 20	mA
switch clamping current	I_{SK}	$V_{SW} < -0.5 \text{ V}$ or $V_{SW} > V_{CC} + 0.5 \text{ V}$	-	± 20	mA
switch current	I_{SW}	$-0.5 \text{ V} < V_{SW} < V_{CC} + 0.5 \text{ V}$	-	± 25	mA
supply current	I_{EE}	-	-	± 20	mA
supply current	I_{CC}	-	-	50	mA
ground current	I_{GND}	-	-	-50	mA
storage temperature	T_{stg}	-	-65	+150	°C
total power dissipation	P_{tot}	-	-	500	mW
power dissipation	P	per switch	-	100	mW
Soldering temperature	T_L	10s	DIP	245	°C
			SOP/SSOP/TSSOP	260	°C

Note:

[1] To avoid drawing V_{CC} current out of terminal nZ, when switch current flows into terminals nYn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no V_{CC} current will flow out of terminals nYn, and in this case there is no limit for the voltage drop across the switch, but the voltages at nYn and nZ may not exceed V_{CC} or V_{EE} .

3.2、Recommended Operating Conditions

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
74HC4052						
supply voltage	V _{CC}	V _{CC} - GND	3.0	5.0	9.0	V
		V _{CC} - V _{EE}	3.0	5.0	9.0	V
input voltage	V _I	-	0	-	V _{CC}	V
switch voltage	V _{SW}	-	V _{EE}	-	V _{CC}	V
ambient temperature	T _{amb}	in free air	-40	-	+125	°C
input transition rise and fall rate	Δt/ΔV	V _{CC} = 4.5 V	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	ns/V
		V _{CC} = 9.0 V	-	-	31	ns/V
74HCT4052						
supply voltage	V _{CC}	V _{CC} - GND	4.5	5.0	5.5	V
		V _{CC} - V _{EE}	3.0	5.0	9.0	V
input voltage	V _I	-	0	-	V _{CC}	V
switch voltage	V _{SW}	-	V _{EE}	-	V _{CC}	V
ambient temperature	T _{amb}	in free air	-40	-	+125	°C
input transition rise and fall rate	Δt/ΔV	V _{CC} = 4.5 V	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	-	ns/V
		V _{CC} = 9.0 V	-	-	-	ns/V

3.3、Electrical Characteristics

3.3.1、DC Characteristics 1

($T_{amb} = -40^{\circ}\text{C} \sim 85^{\circ}\text{C}$, voltages are reference to GND (ground=0V), unless otherwise specified, unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ. ^[1]	Max.	Unit
ON resistance (peak)	R _{ON(peak)}	V _{is} = V _{CC} to V _{EE} ; I _{SW} = 1000 uA	V _{CC} = 4.5 V; V _{EE} = 0 V	-	100	225	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	90	200	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	70	165	Ω
ON resistance (rail)	R _{ON(rail)}	V _{is} = V _{EE} ; I _{SW} = 1000 uA	V _{CC} = 4.5 V; V _{EE} = 0 V	-	80	175	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	70	150	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	60	130	Ω
		V _{is} = V _{CC} ; I _{SW} = 1000 uA	V _{CC} = 4.5 V; V _{EE} = 0 V	-	90	200	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	80	175	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	65	150	Ω
ON resistance mismatch between channels	ΔR _{ON}	V _{is} = V _{CC} to V _{EE}	V _{CC} = 4.5 V; V _{EE} = 0 V	-	9	-	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	8	-	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	6	-	Ω
74HC4052							
HIGH-level input voltage	V _{IH}	V _{CC} = 4.5 V		3.15	2.4	-	V
		V _{CC} = 6.0 V		4.2	3.2	-	V
		V _{CC} = 9.0 V		6.3	4.7	-	V
LOW-level input voltage	V _{IL}	V _{CC} = 4.5 V		-	2.1	1.35	V
		V _{CC} = 6.0 V		-	2.8	1.8	V
		V _{CC} = 9.0 V		-	4.3	2.7	V
input leakage current	I _I	V _{EE} = 0 V; V _I = V _{CC} or GND	V _{CC} = 6.0 V	-	-	±1.0	uA
			V _{CC} = 9.0 V	-	-	±2.0	uA

OFF-state leakage current	$I_{S(OFF)}$	$V_{CC}=9.0\text{ V};$ $V_{EE}=0\text{ V};$ $V_I=V_{IH}\text{ or }V_{IL};$ $ V_{SW} =V_{CC}-V_{EE};$ see Figure 7		per channel	-	-	± 1.0	μA
				all channels	-	-	± 2.0	μA
ON-state leakage current	$I_{S(ON)}$	$V_I=V_{IH}\text{ or }V_{IL}; V_{SW} =V_{CC}-V_{EE};$ $V_{CC}=9.0\text{ V};V_{EE}=0\text{ V};$ see Figure 8			-	-	± 2.0	μA
supply current	I_{CC}	$V_{EE}=0\text{ V};$ $V_I=V_{CC}\text{ or GND};$ $V_{is}=V_{EE}\text{ or }V_{CC};$ $V_{os}=V_{CC}\text{ or }V_{EE}$		$V_{CC}=6.0\text{ V}$	-	-	80.0	μA
				$V_{CC}=9.0\text{ V}$	-	-	160.0	μA
input capacitance	C_I	-			-	3.5	-	pF
switch capacitance	C_{SW}	independent pins nYn			-	5	-	pF
		common pins nZ			-	12	-	pF
74HCT4052								
HIGH-level input voltage	V_{IH}	$V_{CC}=4.5\text{ V to }5.5\text{ V}$			2.0	1.6	-	V
LOW-level input voltage	V_{IL}	$V_{CC}=4.5\text{ V to }5.5\text{ V}$			-	1.2	0.8	V
input leakage current	I_I	$V_I=V_{CC}\text{ or GND};$ $V_{CC}=5.5\text{ V}; V_{EE}=0\text{ V}$			-	-	± 1.0	μA
OFF-state leakage current	$I_{S(OFF)}$	$V_{CC}=9.0\text{ V};$ $V_{EE}=0\text{ V};$ $V_I=V_{IH}\text{ or }V_{IL};$ $ V_{SW} =V_{CC}-V_{EE};$ see Figure 7		per channel	-	-	± 1.0	μA
				all channels	-	-	± 2.0	μA
ON-state leakage current	$I_{S(ON)}$	$V_{CC}=9.0\text{ V};V_{EE}=0\text{ V};$ $V_I=V_{IH}\text{ or }V_{IL}; V_{SW} =V_{CC}-V_{EE};$ see Figure 8			-	-	± 2.0	μA
supply current	I_{CC}	$V_I=V_{CC}\text{ or GND};$ $V_{is}=V_{EE}\text{ or }V_{CC};$ $V_{os}=V_{CC}\text{ or }V_{EE}$		$V_{CC}=5.5\text{V};$ $V_{EE}=0\text{ V}$	-	-	80.0	μA
				$V_{CC}=4.5\text{V};$ $V_{EE}=-4.5\text{V}$	-	-	160.0	μA
additional supply current	ΔI_{CC}	per input; $V_I=V_{CC}-2.1\text{V};$ other inputs at $V_{CC}\text{ or GND};$ $V_{CC}=4.5\text{ V to }5.5\text{ V}; V_{EE}=0\text{ V}$			-	45	202.5	μA
input capacitance	C_I	-			-	3.5	-	pF
switch capacitance	C_{SW}	independent pins nYn			-	5	-	pF
		common pins nZ			-	12	-	pF

Note:

[1] All typical values are measured at $T_{amb} = 25^{\circ}\text{C}$.

[2] $V_I = V_{IH}$ or V_{IL} ; for test circuit see Figure 5.

[3] V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.

[4] V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

3.3.2、DC Characteristics 2

($T_{amb} = -40^{\circ}\text{C} \sim 125^{\circ}\text{C}$, voltages are reference to GND (ground=0V), unless otherwise specified, unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ. ^[1]	Max.	Unit
ON resistance (peak)	R _{ON(peak)}	V _{is} = V _{CC} to V _{EE} ; I _{SW} = 1000 uA	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	270	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	-	240	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	195	Ω
ON resistance (rail)	R _{ON(rail)}	V _{is} = V _{EE} ; I _{SW} = 1000 uA	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	210	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	-	180	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	160	Ω
		V _{is} = V _{CC} ; I _{SW} = 1000 uA	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	240	Ω
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	-	210	Ω
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	180	Ω
74HC4052							
HIGH-level input voltage	V _{IH}	V _{CC} = 4.5 V		3.15	-	-	V
		V _{CC} = 6.0 V		4.2	-	-	V
		V _{CC} = 9.0 V		6.3	-	-	V
LOW-level input voltage	V _{IL}	V _{CC} = 4.5 V		-	-	1.35	V
		V _{CC} = 6.0 V		-	-	1.8	V
		V _{CC} = 9.0 V		-	-	2.7	V
input leakage current	I _I	V _{EE} = 0 V; V _I = V _{CC} or GND	V _{CC} = 6.0 V	-	-	±1.0	uA
			V _{CC} = 9.0 V	-	-	±2.0	uA
OFF-state leakage current	I _{S(OFF)}	V _{CC} = 9.0 V; V _{EE} = 0 V; V _I = V _{IH} or V _{IL} ; V _{SW} = V _{CC} - V _{EE} ;	per channel	-	-	±1.0	uA
			all channels	-	-	±2.0	uA

		see Figure 7					
ON-state leakage current	$I_{S(ON)}$	$V_I = V_{IH} \text{ or } V_{IL}; V_{SW} = V_{CC} - V_{EE};$ $V_{CC} = 9.0 \text{ V}; V_{EE} = 0 \text{ V};$ see Figure 8		-	-	± 2.0	μA
supply current	I_{CC}	$V_{EE} = 0 \text{ V};$ $V_I = V_{CC} \text{ or } \text{GND};$ $V_{is} = V_{EE} \text{ or } V_{CC};$ $V_{os} = V_{CC} \text{ or } V_{EE}$	$V_{CC} = 6.0 \text{ V}$	-	-	160.0	μA
			$V_{CC} = 9.0 \text{ V}$	-	-	320.0	μA
74HCT4052							
HIGH-level input voltage	V_{IH}	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		2.0	-	-	V
LOW-level input voltage	V_{IL}	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		-	-	0.8	V
input leakage current	I_I	$V_I = V_{CC} \text{ or } \text{GND};$ $V_{CC} = 5.5 \text{ V}; V_{EE} = 0 \text{ V}$		-	-	± 1.0	μA
OFF-state leakage current	$I_{S(OFF)}$	$V_{CC} = 9.0 \text{ V};$ $V_{EE} = 0 \text{ V};$ $V_I = V_{IH} \text{ or } V_{IL};$ $ V_{SW} = V_{CC} - V_{EE};$ see Figure 7	per channel	-	-	± 1.0	μA
			all channels	-	-	± 2.0	μA
ON-state leakage current	$I_{S(ON)}$	$V_{CC} = 9.0 \text{ V}; V_{EE} = 0 \text{ V};$ $V_I = V_{IH} \text{ or } V_{IL}; V_{SW} = V_{CC} - V_{EE};$ see Figure 8		-	-	± 2.0	μA
supply current	I_{CC}	$V_I = V_{CC} \text{ or } \text{GND};$ $V_{is} = V_{EE} \text{ or } V_{CC};$ $V_{os} = V_{CC} \text{ or } V_{EE}$	$V_{CC} = 5.5 \text{ V};$ $V_{EE} = 0 \text{ V}$	-	-	160.0	μA
			$V_{CC} = 4.5 \text{ V};$ $V_{EE} = -4.5 \text{ V}$	-	-	320.0	μA
additional supply current	ΔI_{CC}	per input; $V_I = V_{CC} - 2.1 \text{ V};$ other inputs at $V_{CC} \text{ or } \text{GND};$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; V_{EE} = 0 \text{ V}$		-	-	220.5	μA

Note:

[1] All typical values are measured at $T_{amb} = 25^\circ\text{C}$.

[2] $V_I = V_{IH} \text{ or } V_{IL}$; for test circuit see Figure 5.

[3] V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.

[4] V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

3.3.3、AC Characteristics 1

($T_{amb} = -40^{\circ}\text{C} \sim +85^{\circ}\text{C}$; $GND = 0\text{ V}$; $t_r = t_f = 6\text{ ns}$; $C_L = 50\text{ pF}$; unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ. ^[1]	Max.	Unit	
74HC4052							
propagation delay	t _{pd}	V _{is} to V _{os} ; R _L = ∞ Ω; see Figure 9 ^[2]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	5	15	ns
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	4	13	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	4	10	ns
turn-on time	t _{on}	$\bar{E}$, Sn to V _{os} ; R _L = ∞ Ω; see Figure 10 ^[3]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	38	81	ns
			V _{CC} = 5.0 V; V _{EE} =0V; C _L =15pF	-	28	-	ns
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	30	69	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	26	58	ns
turn-off time	t _{off}	$\bar{E}$, Sn to V _{os} ; R _L = 1 kΩ; see Figure 10 ^[4]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	27	63	ns
			V _{CC} = 5.0 V; V _{EE} =0V; C _L =15pF	-	21	-	ns
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	22	54	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	22	48	ns
power dissipation capacitance	C _{PD}	per switch;V _I = GND to V _{CC} ^[5]	-	57	-	pF	
74HCT4052							
propagation delay	t _{pd}	V _{is} to V _{os} ; R _L = ∞ Ω; see Figure 9 ^[2]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	5	15	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	4	10	ns
turn-on time	t _{on}	$\bar{E}$, Sn to V _{os} ; R _L = 1kΩ; see Figure 10 ^[3]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	41	88	ns
			V _{CC} = 5.0 V; V _{EE} =0V; C _L =15pF	-	18	-	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	28	60	ns

turn-off time	t_{off}	$\bar{E}$, Sn to V_{os} ; $R_L = 1\text{ k}\Omega$; see Figure 10 ^[4]	$V_{CC} = 4.5\text{ V}$; $V_{EE} = 0\text{ V}$	-	26	63	ns
			$V_{CC} = 5.0\text{ V}$; $V_{EE} = 0\text{ V}$; $C_L = 15\text{ pF}$	-	13	-	ns
			$V_{CC} = 4.5\text{ V}$; $V_{EE} = -4.5\text{ V}$	-	21	48	ns
power dissipation capacitance	C_{PD}	per switch; $V_I = \text{GND to } V_{CC} - 1.5\text{ V}$ ^[5]	-	-	57	-	pF

Note:

[1] All typical values are measured at $T_{amb} = 25^\circ\text{C}$.

[2] t_{pd} is the same as t_{pHL} and t_{pLH} .

[3] t_{on} is the same as t_{pZH} and t_{pZL} .

[4] t_{off} is the same as t_{pHZ} and t_{pLZ} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma\{(C_L + C_{SW}) \times V_{CC}^2 \times f_o\}$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

N = number of inputs switching;

$\Sigma\{(C_L + C_{SW}) \times V_{CC}^2 \times f_o\}$ = sum of outputs;

C_L = output load capacitance in pF;

C_{SW} = switch capacitance in pF;

V_{CC} = supply voltage in V.

[6] For test circuit see Figure 11.

[7] V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.

[8] V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

3.3.4、AC Characteristics 2

($T_{amb} = -40^{\circ}\text{C} \sim +125^{\circ}\text{C}$; $GND = 0\text{ V}$; $t_r = t_f = 6\text{ ns}$; $C_L = 50\text{ pF}$; unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ. ^[1]	Max.	Unit	
74HC4052							
propagation delay	t _{pd}	V _{is} to V _{os} ; R _L = ∞ Ω; see Figure 9 ^[2]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	18	ns
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	-	15	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	12	ns
turn-on time	t _{on}	$\bar{E}$, Sn to V _{os} ; R _L = ∞ Ω; see Figure 10 ^[3]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	98	ns
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	-	83	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	69	ns
turn-off time	t _{off}	$\bar{E}$, Sn to V _{os} ; R _L = 1 kΩ; see Figure 10 ^[4]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	75	ns
			V _{CC} = 6.0 V; V _{EE} = 0 V	-	-	64	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	57	ns
74HCT4052							
propagation delay	t _{pd}	V _{is} to V _{os} ; R _L = ∞ Ω; see Figure 9 ^[2]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	18	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	12	ns
turn-on time	t _{on}	$\bar{E}$, Sn to V _{os} ; R _L = 1kΩ; see Figure 10 ^[3]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	105	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	72	ns
turn-off time	t _{off}	$\bar{E}$, Sn to V _{os} ; R _L = 1 kΩ; see Figure 10 ^[4]	V _{CC} = 4.5 V; V _{EE} = 0 V	-	-	75	ns
			V _{CC} = 4.5 V; V _{EE} = -4.5 V	-	-	57	ns

Note:

[1] All typical values are measured at $T_{amb} = 25^{\circ}\text{C}$.

[2] t_{pd} is the same as t_{PHL} and t_{PLH} .

[3] t_{on} is the same as t_{PZH} and t_{PZL} .

[4] t_{off} is the same as t_{PHZ} and t_{PLZ} .

[5] For test circuit see Figure 11.

[6] V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.

[7] V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

3.3.5、AC Characteristics 3

($T_{amb} = 25^{\circ}\text{C}$; $GND = 0\text{V}$; $C_L = 50\text{pF}$; recommended conditions and typical values.)

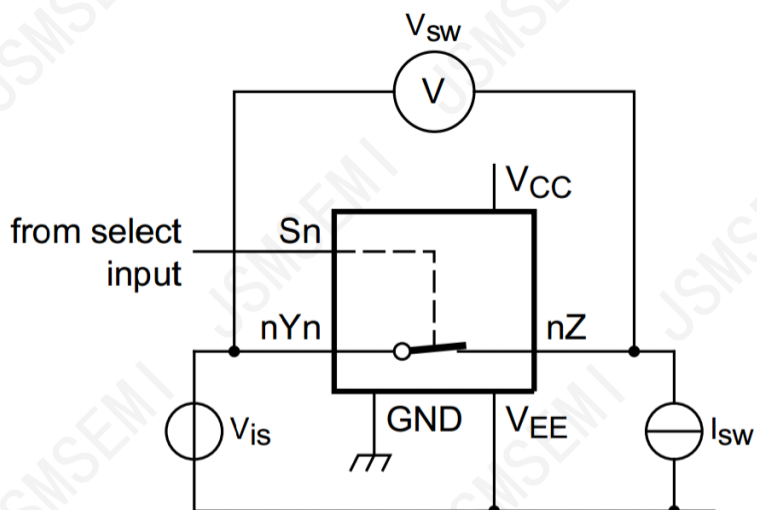
Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
sine-wave distortion	d_{sin}	$f_i = 1\text{ kHz};$ $R_L = 10\text{ k}\Omega;$ see Figure 12	$V_{is} = 4.0\text{ V (p-p)};$ $V_{CC} = 2.25\text{ V};$ $V_{EE} = -2.25\text{ V}$	-	0.04	-	%
			$V_{is} = 8.0\text{ V (p-p)};$ $V_{CC} = 4.5\text{ V};$ $V_{EE} = -4.5\text{ V}$	-	0.02	-	%
		$f_i = 10\text{ kHz};$ $R_L = 10\text{ k}\Omega;$ see Figure 12	$V_{is} = 4.0\text{ V (p-p)};$ $V_{CC} = 2.25\text{ V};$ $V_{EE} = -2.25\text{ V}$	-	0.12	-	%
			$V_{is} = 8.0\text{ V (p-p)};$ $V_{CC} = 4.5\text{ V};$ $V_{EE} = -4.5\text{ V}$	-	0.06	-	%
isolation (OFF-state)	α_{iso}	$R_L = 600\text{ }\Omega;$ $f_i = 1\text{ MHz};$ see Figure 13	$V_{CC} = 2.25\text{ V};$ ^[1] $V_{EE} = -2.25\text{ V}$	-	-50	-	dB
			$V_{CC} = 4.5\text{ V};$ ^[1] $V_{EE} = -4.5\text{ V}$	-	-50	-	dB
crosstalk	Xtalk	between two switches/multiplexers; $R_L = 600\text{ }\Omega; f_i = 1\text{ MHz};$ see Figure 14	$V_{CC} = 2.25\text{ V};$ ^[1] $V_{EE} = -2.25\text{ V}$	-	-60	-	dB
			$V_{CC} = 4.5\text{ V};$ ^[1] $V_{EE} = -4.5\text{ V}$	-	-60	-	dB
crosstalk voltage	V_{ct}	peak-to-peak value; between control and any switch; $R_L = 600\text{ }\Omega; f_i = 1\text{ MHz};$ $\bar{E}$ or Sn square wave between V_{CC} and GND; $t_r = t_f = 6\text{ ns};$ see Figure 15	$V_{CC} = 4.5\text{ V};$ $V_{EE} = 0\text{ V}$	-	110	-	mV
			$V_{CC} = 4.5\text{ V};$ $V_{EE} = -4.5\text{ V}$	-	220	-	mV
-3dB frequency response	$f_{(-3dB)}$	$R_L = 50\text{ }\Omega;$ see Figure 16	$V_{CC} = 2.25\text{ V};$ ^[2] $V_{EE} = -2.25\text{ V}$	-	170	-	MHz
			$V_{CC} = 4.5\text{ V};$ ^[2] $V_{EE} = -4.5\text{ V}$	-	180	-	MHz

Note:

- [1] Adjust input voltage V_{is} to 0 dBm level (0 dBm = 1 mW into 600 Ω).
 [2] Adjust input voltage V_{is} to 0 dBm level at V_{os} for 1 MHz (0 dBm = 1 mW into 50 Ω).
 [3] V_{is} is the input voltage at a nYn or nZ terminal, whichever is assigned as an input.
 [4] V_{os} is the output voltage at a nYn or nZ terminal, whichever is assigned as an output.

4、Testing Circuit

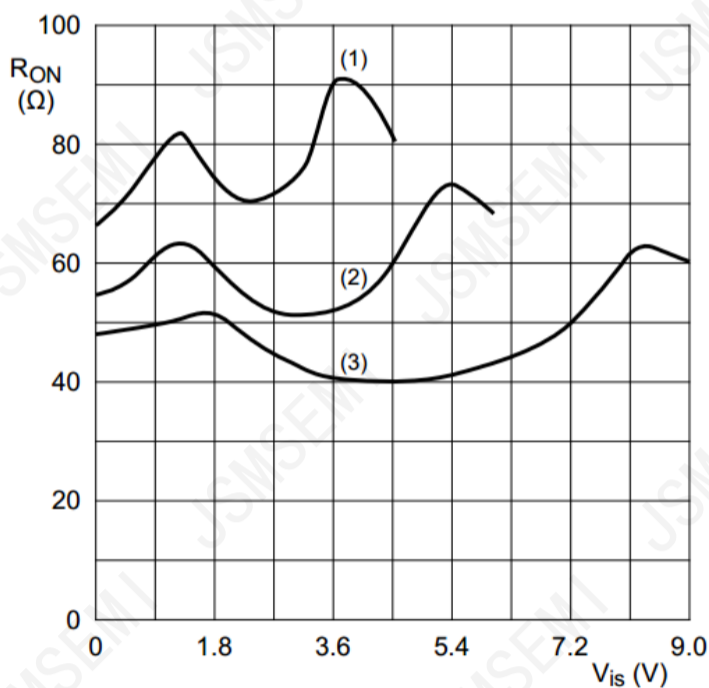
4.1、DC Testing Circuit 1



$$V_{IS} = 0V \text{ to } (V_{CC} - V_{EE})$$

$$R_{ON} = V_{SW} / I_{SW}$$

Figure 5. Test circuit for measuring R_{ON}



$$V_{IS} = 0V \text{ to } (V_{CC} - V_{EE})$$

$$(1) V_{CC} = 4.5V$$

$$(2) V_{CC} = 6V$$

$$(3) V_{CC} = 9V$$

Figure 6. Typical R_{ON} as a function of input voltage V_{IS}

4.2、DC Testing Circuit 2

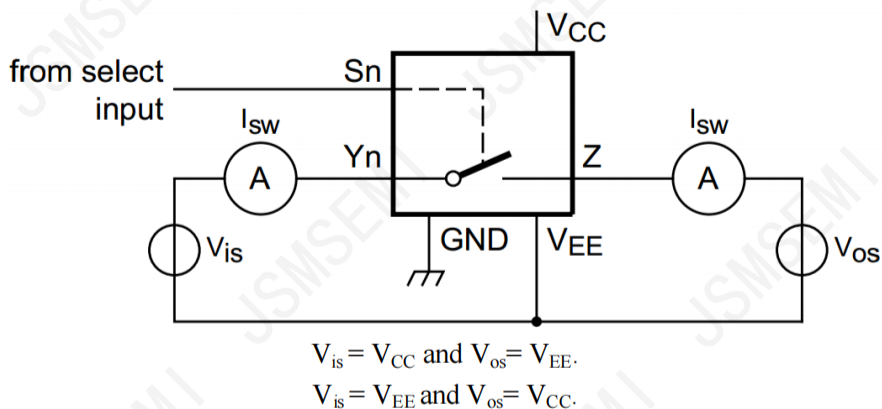


Figure 7. Test circuit for measuring OFF-state current

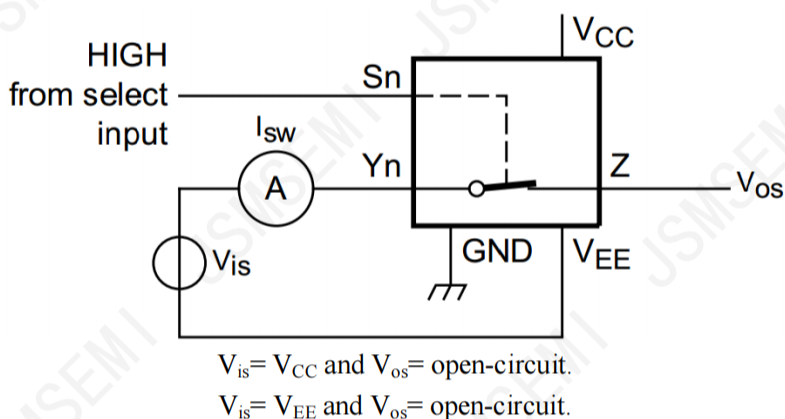


Figure 8. Test circuit for measuring ON-state current

4.3、AC Testing Waveforms

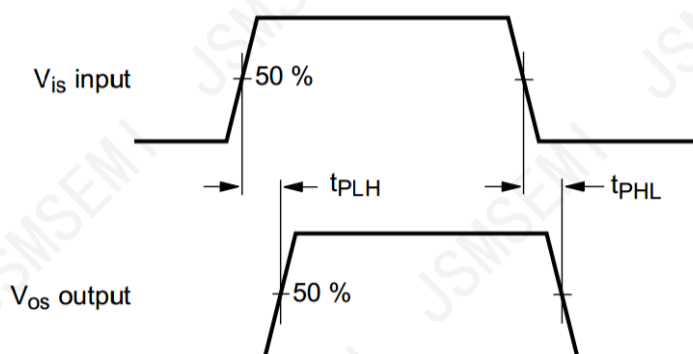


Figure 9. Input (V_{is}) to output (V_{os}) propagation delays

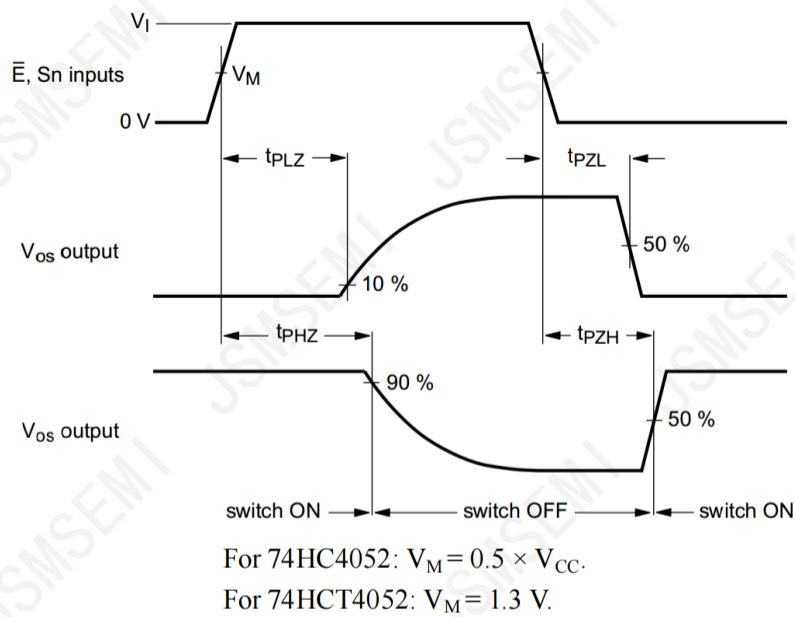


Figure 10. Turn-on and turn-off times

4.4. AC Testing Circuit 1

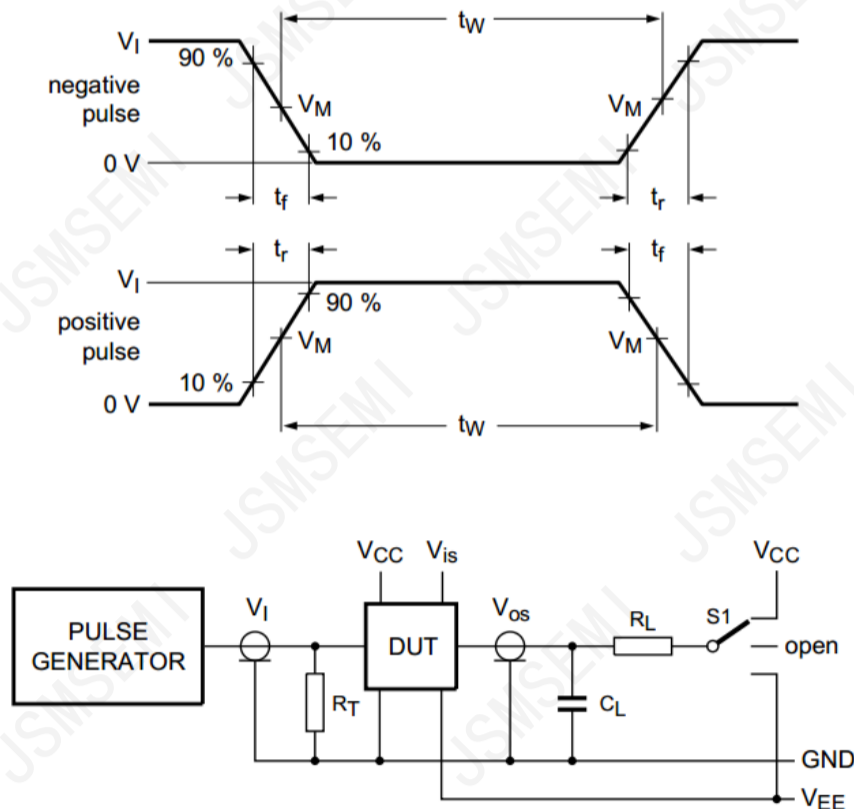


Figure 11. Test circuit for measuring switching times

Definitions for test circuit:

R_T = termination resistance should be equal to the output impedance Z_O of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

R_L = load resistance.

S1 = Test selection switch.

4.5、Test Data

Test	Input				Load		S1 position
	V _I	V _{is}	t _r , t _f		C _L	R _L	
			at f _{max}	other ^[1]			
t _{PHL} , t _{PLH}	[2]	pulse	< 2ns	6ns	50pF	1kΩ	open
t _{PZH} , t _{PHZ}	[2]	V _{CC}	< 2ns	6ns	50pF	1kΩ	V _{EE}
t _{PZL} , t _{PLZ}	[2]	V _{EE}	< 2ns	6ns	50pF	1kΩ	V _{CC}

Note:

[1] $t_r = t_f = 6$ ns; when measuring f_{max} , there is no constraint to t_r and t_f with 50 % duty factor.

[2] V_I values:

For 74HC4052: $V_I = V_{CC}$.

For 74HCT4052: $V_I = 3V$.

4.6、AC Testing Circuit 2

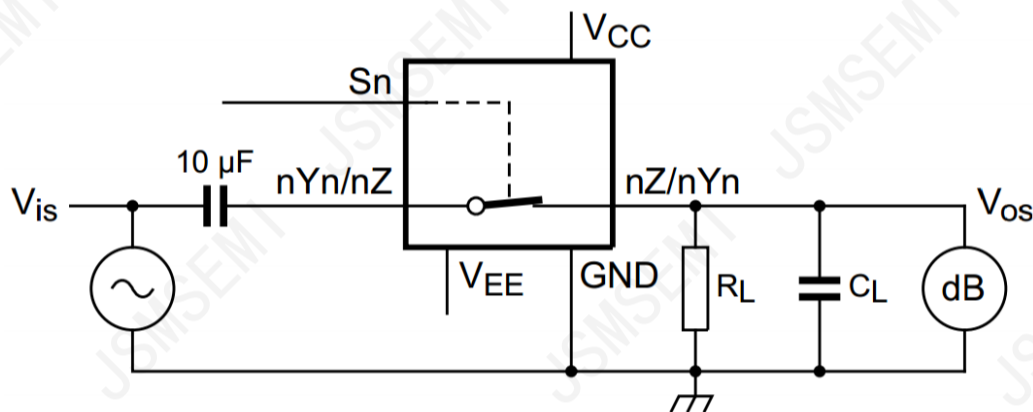
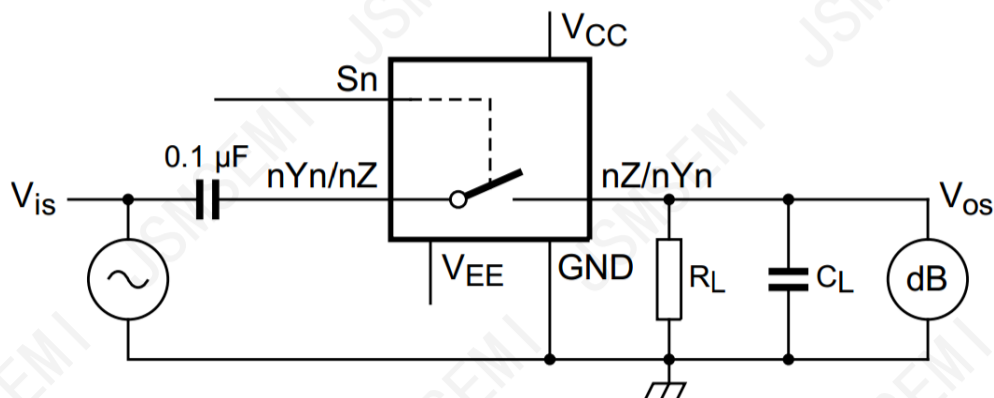
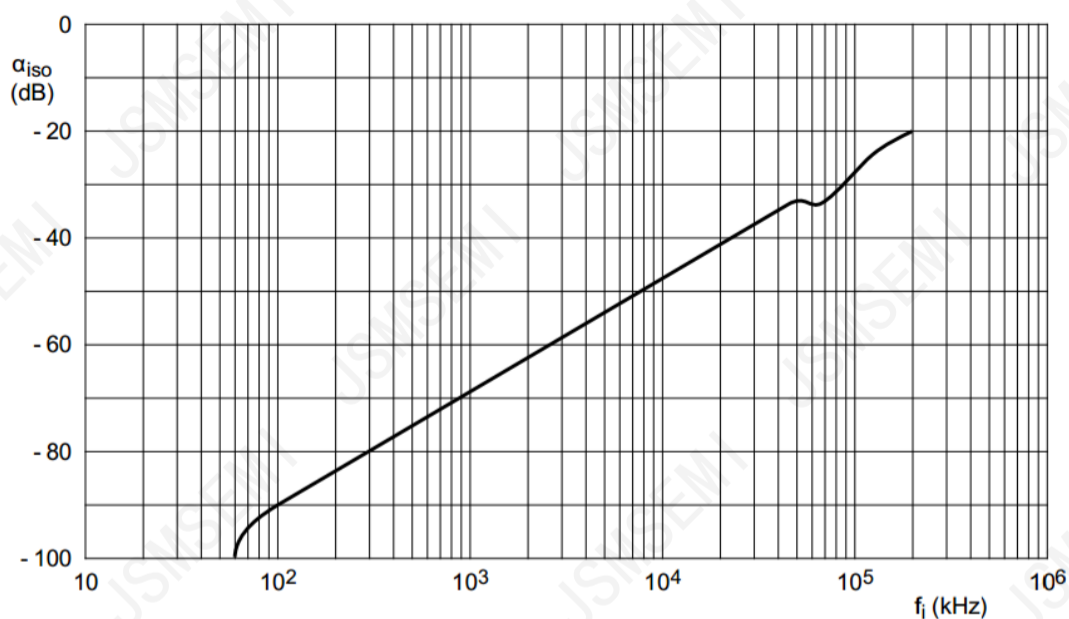


Figure 12. Test circuit for measuring sine-wave distortion



$V_{CC} = 4.5$ V; $GND = 0$ V; $V_{EE} = -4.5$ V; $R_L = 600$ Ω ; $R_S = 1$ k Ω .

a. Test circuit



b. Isolation (OFF-state) as a function of frequency

Figure 13. Test circuit for measuring isolation (OFF-state)

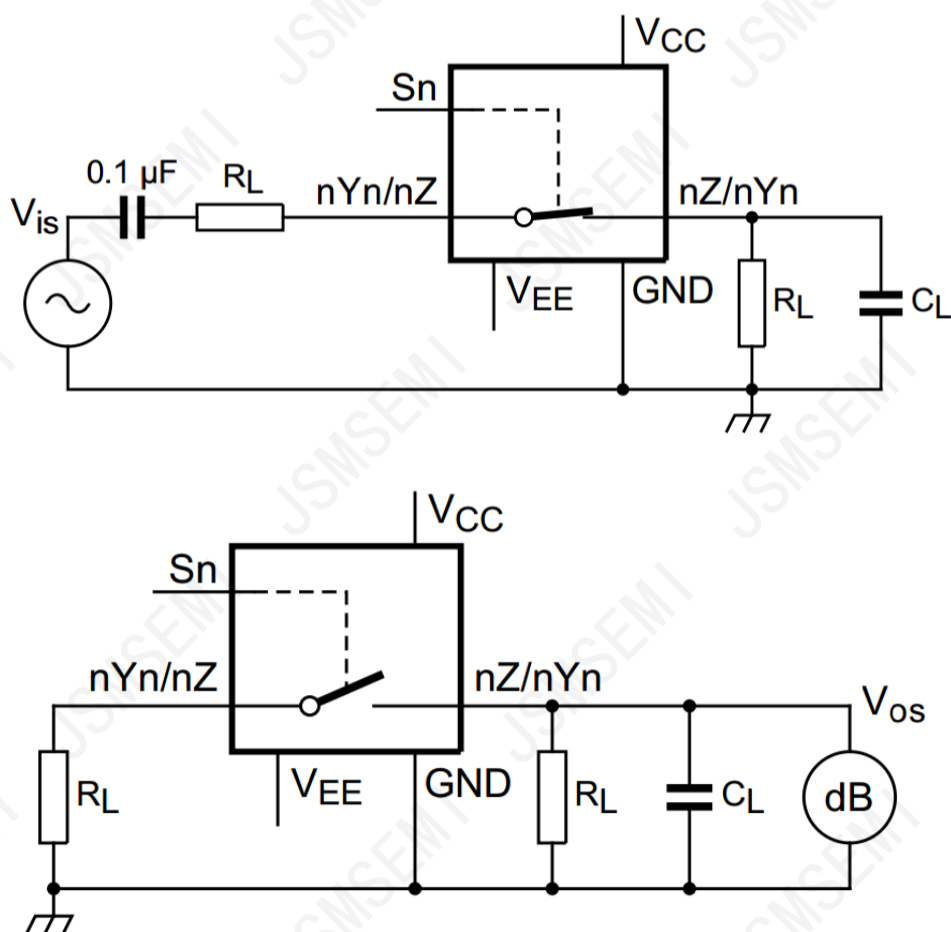


Figure 14. Test circuits for measuring crosstalk between any two switches/multiplexers

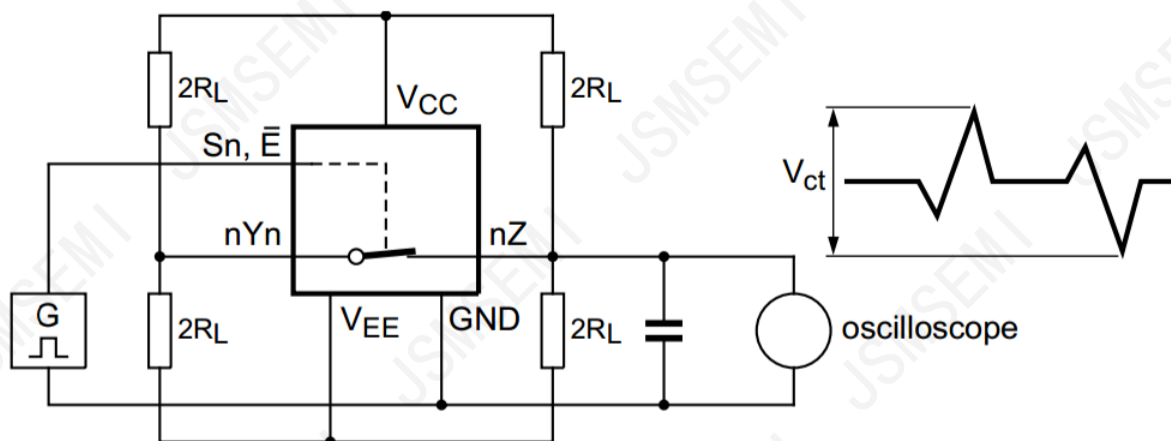
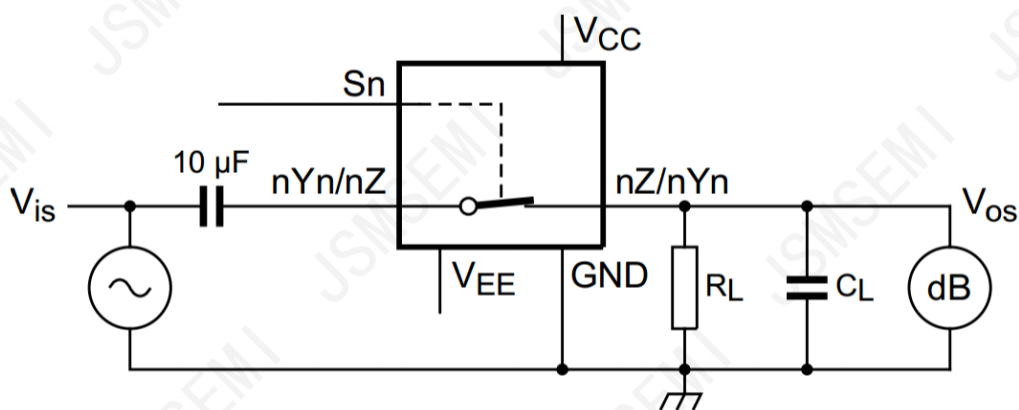
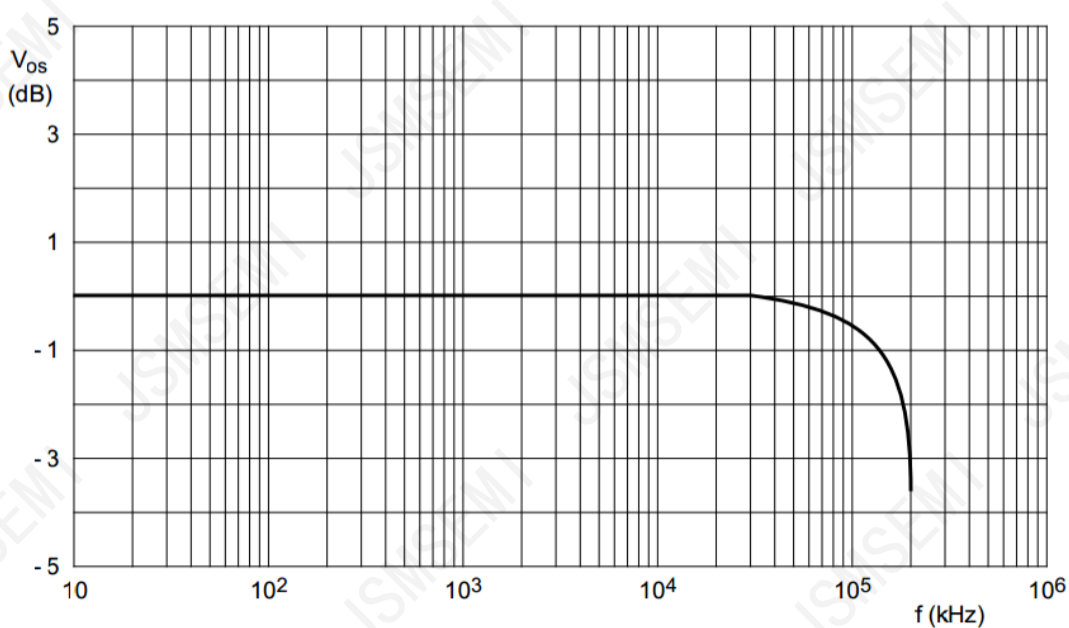


Figure 15. Test circuit for measuring crosstalk between control input and any switch



$V_{CC} = 4.5 \text{ V}$; $GND = 0 \text{ V}$; $V_{EE} = -4.5 \text{ V}$; $R_L = 50 \Omega$; $R_S = 1 \text{ k}\Omega$

a. Test circuit

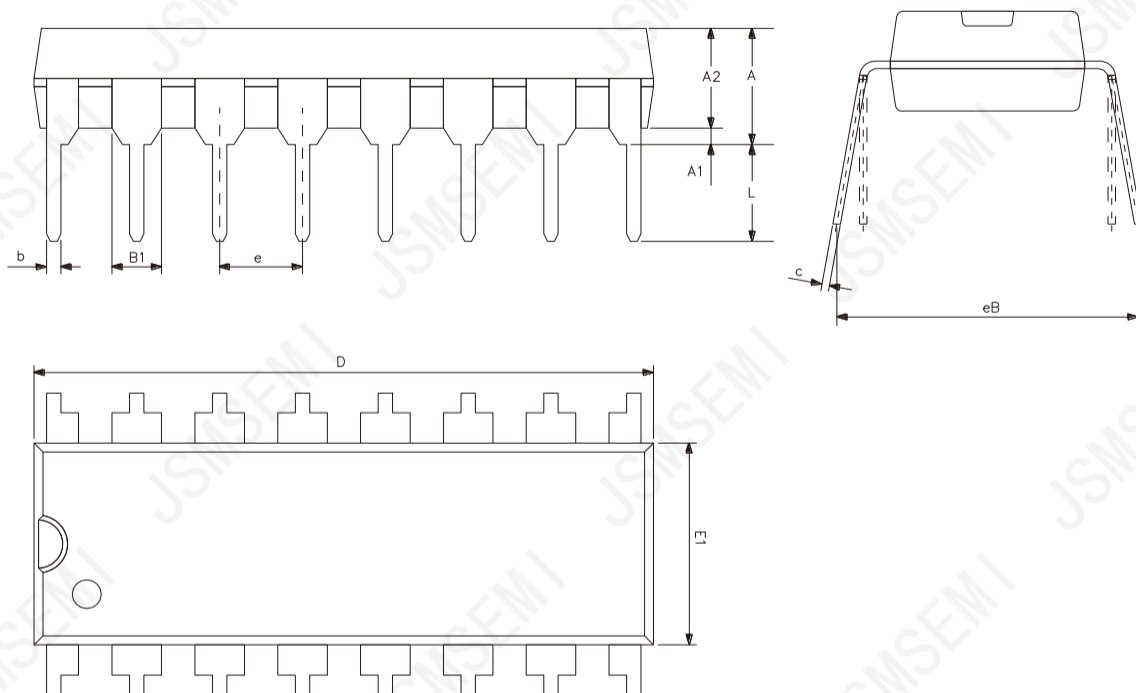


b. Typical frequency response

Figure 16. Test circuit for frequency response

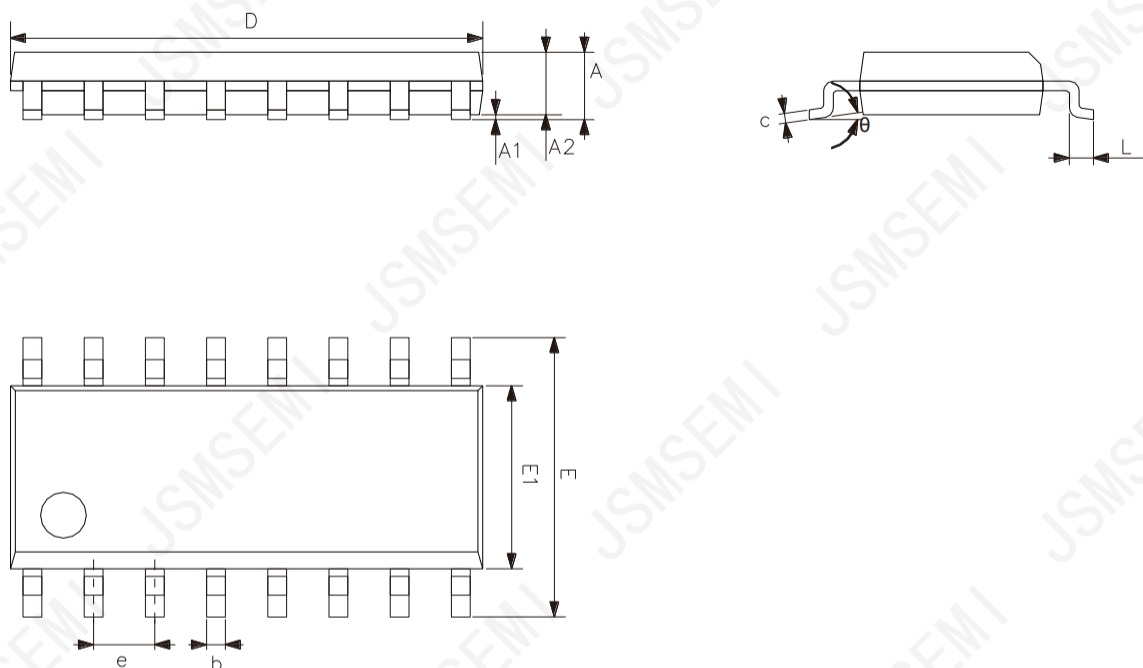
5、Package Information

5.1、DIP16



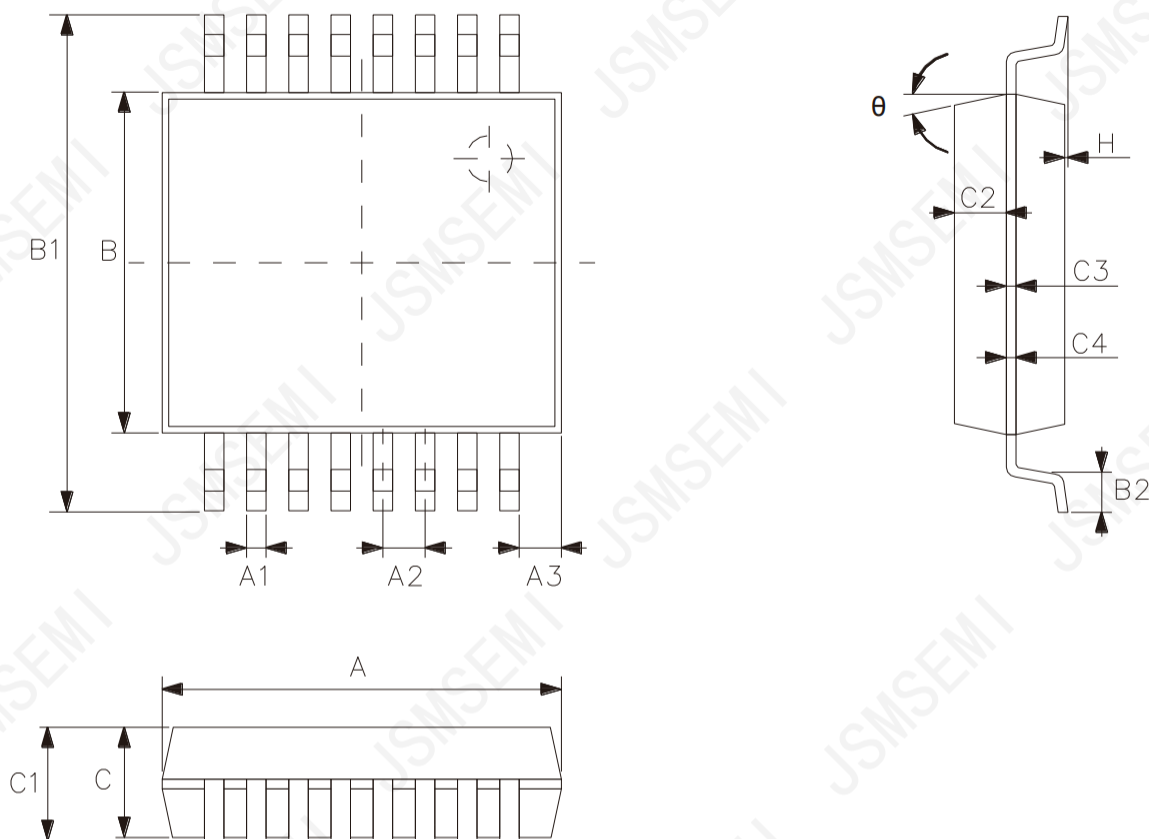
Symbol	Dimensions (mm)	
	Min.	Max.
A2	3.20	3.60
A1	0.51	-
A	3.60	5.33
L	3.00	3.60
b	0.36	0.56
B1	1.52	
D	18.80	19.94
E1	6.20	6.60
e	2.54	
c	0.20	0.36
eB	7.62	9.30

5.2、SOP16



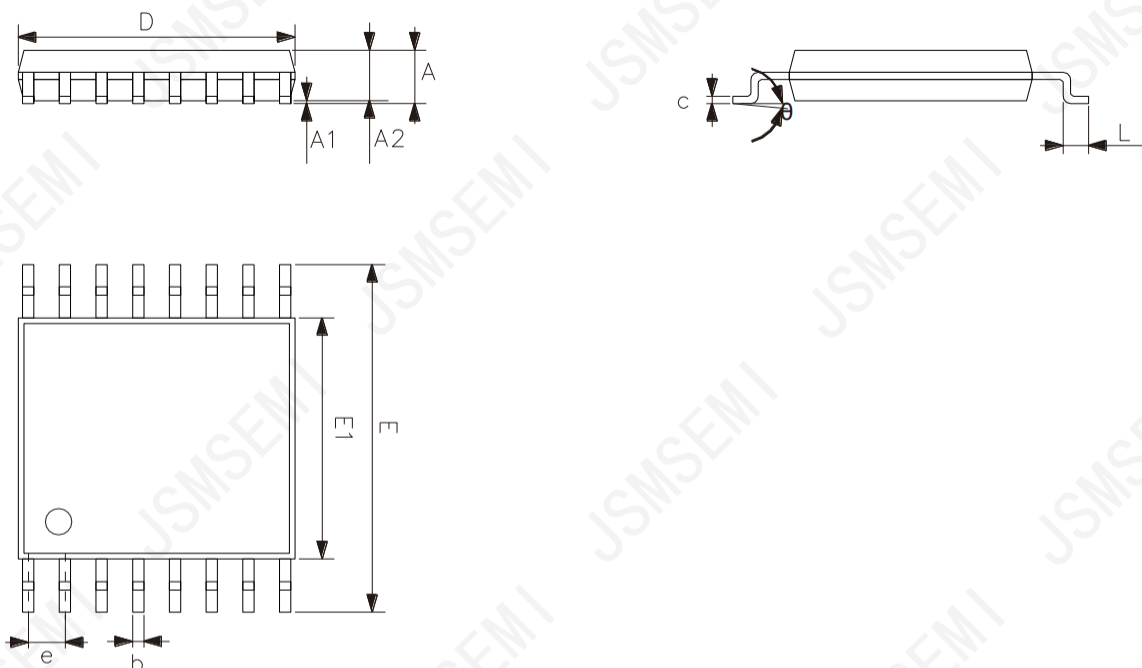
Symbol	Dimensions (mm)	
	Min.	Max.
A	1.35	1.80
A1	0.10	0.25
A2	1.25	1.55
b	0.33	0.51
c	0.19	0.25
D	9.50	10.10
E	5.80	6.30
E1	3.70	4.10
e	1.27	
L	0.35	0.89
θ	0°	8°

5.3、SSOP16



Symbol	Dimensions (mm)	
	Min.	Max.
A	6.15	6.25
A1	0.30	
A2	0.65	
A3	0.675	
B	5.25	5.35
B1	7.65	7.95
B2	0.60	0.80
C	1.70	1.80
C1	1.75	1.95
C2	0.80	
C3	0.15	
C4	0.17	
H	0.05	0.15
θ	0°	8°

5.4、TSSOP16



Symbol	Dimensions (mm)	
	Min.	Max.
A	-	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E1	4.30	4.50
E	6.20	6.60
e	0.65	
L	0.45	0.75
θ	0°	8°

6、Statements And Notes

6.1、The name and content of Hazardous substances or Elements in the product

Part name	Hazardous substances or Elements									
	Lead and lead compounds	Mercury and mercury compounds	Cadmium and cadmium compounds	Hexavalent chromium compounds	Polybrominated biphenyls	Polybrominated biphenyl ethers	Dibutyl phthalate	Butylbenzyl phthalate	Di-2-ethylhexyl phthalate	Diisobutyl phthalate
Lead frame	○	○	○	○	○	○	○	○	○	○
Plastic resin	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
The lead	○	○	○	○	○	○	○	○	○	○
Plastic sheet installed	○	○	○	○	○	○	○	○	○	○
explanation	○: Indicates that the content of hazardous substances or elements in the detection limit of the following the SJ/T11363-2006 standard. ×: Indicates that the content of hazardous substances or elements exceeding the SJ/T11363-2006 Standard limit requirements.									

Important Notice

JSMSEMI Semiconductor (JSMSEMI) PRODUCTS ARE NEITHER DESIGNED NOR INTENDED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS UNLESS THE SPECIFIC JSMSEMI PRODUCTS ARE SPECIFICALLY DESIGNATED BY JSMSEMI FOR SUCH USE. BUYERS ACKNOWLEDGE AND AGREE THAT ANY SUCH USE OF JSMSEMI PRODUCTS WHICH JSMSEMI HAS NOT DESIGNATED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS IS SOLELY AT THE BUYER' S RISK.

JSMSEMI assumes no liability for application assistance or customer product design. Customers are responsible for their products and applications using JSMSEMI products.

Resale of JSMSEMI products or services with statements different from or beyond the parameters stated by JSMSEMI for that product or service voids all express and any implied warranties for the associated JSMSEMI product or service. JSMSEMI is not responsible or liable for any such statements.

JSMSEMI All Rights Reserved. Information and data in this document are owned by JSMSEMI wholly and may not be edited, reproduced, or redistributed in any way without the express written consent from JSMSEMI.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the JSMSEMI product that you intend to use.

For additional information please contact Kevin@jsmsemi.com or visit www.jsmsemi.com